

PMBT3640

PNP 1 GHz switching transistor Rev. 03 — 6 July 2004

Product data sheet



1.1 General description

PNP general purpose switching transistor in a SOT23 package.

1.2 Features

- Volume delivery
- Short lead times
- Smallest packages.

Pinning information 2.

Table 1: **Discrete pinning**

Pin	Description	Simplified outline	Symbol
1	base		_
2	emitter] 3	3
3	collector	1 2 SOT23	1 — 2 sym013

Ordering information 3.

Table 2: Ordering information

Туре	Package				
number	Name	Description	Version		
PMBT3640	-	plastic surface mounted package; 3 leads	SOT23		

Marking 4.

Table 3: **Marking**

Type number	Marking code
PMBT3640	51*

[1] * = p: Made in Hong Kong.

* = t: Made in Malaysia.

* = W: Made in China.





5. Limiting values

Table 4: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-12	V
V_{CEO}	collector-emitter voltage	open base	-	-12	V
V _{EBO}	emitter-base voltage	open collector	-	-4	V
I _C	DC collector current		-	-80	mA
P _{tot}	total power dissipation	up to $T_s = 85 ^{\circ}C$	<u>[1]</u> _	350	mW
T _{stg}	storage temperature		-55	+150	°C
Tj	junction temperature		-	175	°C

^[1] T_s is the temperature at the soldering point of the collector tab.

6. Thermal characteristics

Table 5: Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-s)}$	from junction to soldering point of the collector tab		260	K/W

7. Characteristics

Table 6: Characteristics

 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Off charact	teristics					
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = -100 \ \mu A; \ I_E = 0 \ A$	-12	-	-	V
$V_{(BR)CES}$	collector-emitter breakdown voltage	$I_C = -100 \ \mu A; \ V_{BE} = 0 \ V$	-12	-	-	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_E = -100 \mu A; I_C = 0 A$	-4	-	-	V
I _{CES}	collector cut-off current	$V_{CE} = -6 \text{ V}; V_{BE} = 0 \text{ V}$	-	-	-0.01	μΑ
		$V_{CE} = -6 \text{ V}; V_{BE} = 0 \text{ V};$ $T_{amb} = 65 ^{\circ}\text{C}$	-	-	–1	μΑ
I _B	base current	$V_{CE} = -6 \text{ V}; V_{BE} = 0 \text{ V}$	-	-	-10	nA
On charact	teristics; pulse test: pulse wi	dth ≤ 300 μs and duty cycle ≤ 2 %				
h _{FE}	DC current gain	$I_C = -10 \text{ mA}; V_{CE} = -0.3 \text{ V}$	30	-	120	
		$I_C = -50 \text{ mA}; V_{CE} = -1 \text{ V}$	20	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -1 \text{ mA}$	-	-	-0.2	V
		$I_C = -50 \text{ mA}; I_B = -5 \text{ mA}$	-	-	-0.6	V
		$I_C = -10 \text{ mA}; I_B = -1 \text{ mA};$ $T_{amb} = 65 ^{\circ}\text{C}$	-	-	-0.25	V

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 Table 6:
 Characteristics ...continued

 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{BEsat}	base-emitter saturation	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	-0.75	-	-0.95	V
	voltage	$I_C = -10 \text{ mA}; I_B = -1 \text{ mA}$	-0.8	-	-1	V
		$I_C = -50 \text{ mA}; I_B = -5 \text{ mA}$	-	-	-1.5	V
Small-sigr	nal characteristics					
f _T	transition frequency	$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V};$ f = 100 MHz	500	-	-	MHz
C _c	output capacitance	$I_E = 0 A; V_{CB} = -5 V; f = 1 MHz$	-	-	3.5	pF
C _e	input capacitance	$I_C = 0 \text{ A}; V_{EB} = -0.5 \text{ V};$ f = 1 MHz	-	-	3.5	pF
Switching	times					
t _d	delay time	$V_{CC} = -6 \text{ V; } I_{C} = -50 \text{ mA;}$ $V_{BE(off)} = -1.9 \text{ V; } I_{B1} = -5 \text{ mA}$			10	ns
t _s	storage time	$V_{CC} = -6 \text{ V}; I_C = -50 \text{ mA};$ $I_{B1} = I_{B2} = -5 \text{ mA}$	-	-	20	ns
t _r	rise time	$V_{CC} = -6 \text{ V; } I_C = -50 \text{ mA;}$ $V_{BE(off)} = -1.9 \text{ V; } I_{B1} = -5 \text{ mA}$	-	-	30	ns
t _f	fall time	$V_{CC} = -6 \text{ V}; I_C = -50 \text{ mA};$ $I_{B1} = I_{B2} = -5 \text{ mA}$	-	-	12	ns
t _{on}	turn-on time	$V_{CC} = -6 \text{ V; } I_C = -50 \text{ mA;}$ $V_{BE(off)} = -1.9 \text{ V; } I_{B1} = -5 \text{ mA}$	-	-	25	ns
		$V_{CC} = -1.5 \text{ V}; I_C = -10 \text{ mA};$ $I_{B1} = -0.5 \text{ mA}$	-	-	60	ns
t _{off}	turn-off time	$V_{CC} = -6 \text{ V}; I_C = -50 \text{ mA};$ $V_{BE(off)} = -1.9 \text{ V};$ $I_{B1} = I_{B2} = -5 \text{ mA}$	-	-	35	ns
		$V_{CC} = -1.5 \text{ V}; I_C = -10 \text{ mA};$ $I_{B1} = I_{B2} = -0.5 \text{ mA}$	-	-	75	ns

Package outline

Plastic surface mounted package; 3 leads

SOT23

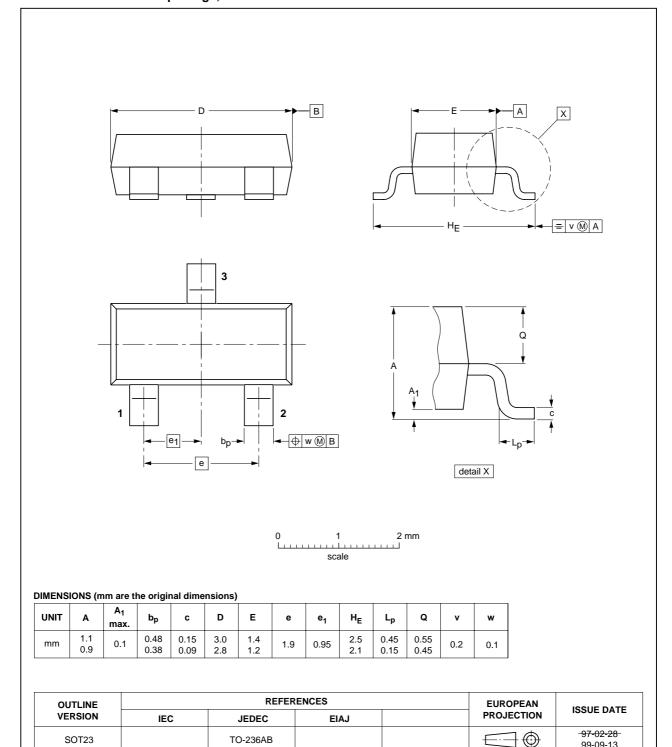


Fig 1. Package outline.

99-09-13





9. Revision history

Table 7: Revision history

Document ID	Release date	Data sheet status	Change notice	Order number	Supersedes
PMBT3640_3	20040706	Product data sheet	-	9397 750 13404	PMBT3640_CNV_2
Modifications:	 The format of this data sheet has information standard of Philips Se Table 3: Marking code changed. Section 1.2: Feature list added. 		-	comply with the cur	rent presentation and
PMBT3640_CNV_2	19950930	Product specification	-	-	-



Level	Data sheet status [1]	Product status [2] [3]	Definition
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PMBT3640

PNP 1 GHz switching transistor

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